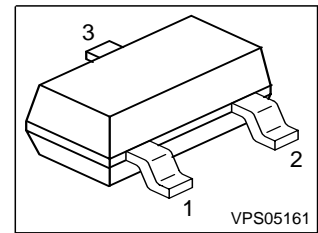


**SIPMOS<sup>®</sup> Small-Signal-Transistor**
**Features**

- P-Channel
- Enhancement mode
- Avalanche rated
- Logic Level
- dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101
- Halogen-free according to IEC61249-2-21

**Product Summary**

Drain source voltage	$V_{DS}$	-60	V
Drain-source on-state resistance	$R_{DS(on)}$	2	$\Omega$
Continuous drain current	$I_D$	-0.33	A



Type	Package	Tape and Reel	Marking	Pin 1	PIN 2	PIN 3
BSS 83 P	PG-SOT-23	H6327: 3000pcs/r.	YAs	G	S	D

**Maximum Ratings**, at  $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_A = 25\text{ °C}$ $T_A = 70\text{ °C}$	$I_D$	-0.33 -0.27	A
Pulsed drain current $T_A = 25\text{ °C}$	$I_D$ puls	-1.32	
Avalanche energy, single pulse $I_D = -0.33\text{ A}$ , $V_{DD} = -25\text{ V}$ , $R_{GS} = 25\ \Omega$	$E_{AS}$	9.5	mJ
Avalanche energy, periodic limited by $T_{jmax}$	$E_{AR}$	0.036	
Reverse diode dv/dt $I_S = -0.33\text{ A}$ , $V_{DS} = -48\text{ V}$ , $di/dt = 200\text{ A}/\mu\text{s}$ , $T_{jmax} = 150\text{ °C}$	dv/dt	6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation $T_A = 25\text{ °C}$	$P_{tot}$	0.36	W
Operating and storage temperature	$T_j$ , $T_{stg}$	-55...+150	$^{\circ}\text{C}$
IEC climatic category; DIN IEC 68-1		55/150/56	
ESD Class; JESD22-A114-HBM		Class 0	

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - soldering point ( Pin 3 )	$R_{thJS}$	-	-	150	K/W
SMD version, device on PCB: @ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>1)</sup>	$R_{thJA}$	-	-	350 300	

**Electrical Characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain- source breakdown voltage $V_{GS} = 0\text{ V}$ , $I_D = -250\text{ }\mu\text{A}$	$V_{(BR)DSS}$	-60	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = -80\text{ }\mu\text{A}$	$V_{GS(th)}$	-1	-1.5	-2	
Zero gate voltage drain current $V_{DS} = -60\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_j = 25\text{ °C}$ $V_{DS} = -60\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_j = 125\text{ °C}$	$I_{DSS}$	-	-0.1 -10	-1 -100	$\mu\text{A}$
Gate-source leakage current $V_{GS} = -20\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GSS}$	-	-10	-100	nA
Drain-source on-state resistance $V_{GS} = -4.5\text{ V}$ , $I_D = -0.27\text{ A}$	$R_{DS(on)}$	-	2	3	$\Omega$
Drain-source on-state resistance $V_{GS} = -10\text{ V}$ , $I_D = -0.33\text{ A}$	$R_{DS(on)}$	-	1.4	2	

<sup>1</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Dynamic Characteristics</b>					
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = -0.27\text{ A}$	$g_{fs}$	0.24	0.47	-	S
Input capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = -25\text{ V}$ , $f = 1\text{ MHz}$	$C_{iss}$	-	62	78	pF
Output capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = -25\text{ V}$ , $f = 1\text{ MHz}$	$C_{oss}$	-	19	24	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = -25\text{ V}$ , $f = 1\text{ MHz}$	$C_{rss}$	-	7	9	
Turn-on delay time $V_{DD} = -30\text{ V}$ , $V_{GS} = -4.5\text{ V}$ , $I_D = -0.27\text{ A}$ , $R_G = 43\text{ }\Omega$	$t_{d(on)}$	-	23	35	ns
Rise time $V_{DD} = -30\text{ V}$ , $V_{GS} = -4.5\text{ V}$ , $I_D = -0.27\text{ A}$ , $R_G = 43\text{ }\Omega$	$t_r$	-	71	106	
Turn-off delay time $V_{DD} = -30\text{ V}$ , $V_{GS} = -4.5\text{ V}$ , $I_D = -0.27\text{ A}$ , $R_G = 43\text{ }\Omega$	$t_{d(off)}$	-	56	70	
Fall time $V_{DD} = -30\text{ V}$ , $V_{GS} = -4.5\text{ V}$ , $I_D = -0.27\text{ A}$ , $R_G = 43\text{ }\Omega$	$t_f$	-	61	76	

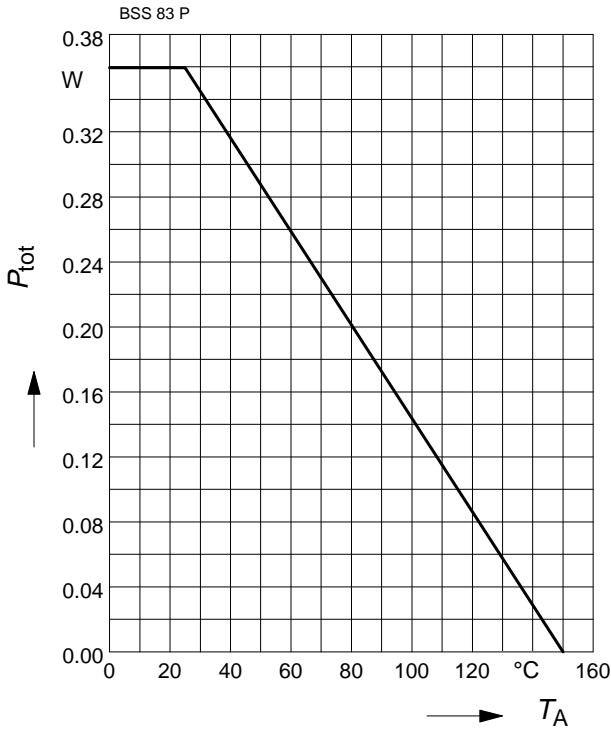
**Electrical Characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Dynamic Characteristics</b>					
Gate to source charge $V_{DD} = -48\text{ V}, I_D = -0.33\text{ A}$	$Q_{gs}$	-	0.12	0.18	nC
Gate to drain charge $V_{DD} = -48\text{ V}, I_D = -0.33\text{ A}$	$Q_{gd}$	-	1.1	1.65	
Gate charge total $V_{DD} = -48\text{ V}, I_D = -0.33\text{ A}, V_{GS} = 0\text{ to }-10\text{ V}$	$Q_g$	-	2.38	3.57	
Gate plateau voltage $V_{DD} = -48\text{ V}, I_D = -0.33\text{ A}$	$V_{(plateau)}$	-	-2.94	-	V

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Reverse Diode</b>					
Inverse diode continuous forward current $T_A = 25\text{ °C}$	$I_S$	-	-	-0.33	A
Inverse diode direct current, pulsed $T_A = 25\text{ °C}$	$I_{SM}$	-	-	-1.32	
Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = -0.33$	$V_{SD}$	-	-0.84	-1.1	V
Reverse recovery time $V_R = -30\text{ V}, I_F = I_S, di_F/dt = 80\text{ A}/\mu\text{s}$	$t_{rr}$	-	59.4	89	ns
Reverse recovery charge $V_R = -30\text{ V}, I_F = I_S, di_F/dt = 80\text{ A}/\mu\text{s}$	$Q_{rr}$	-	37.5	56	nC

**Power Dissipation**

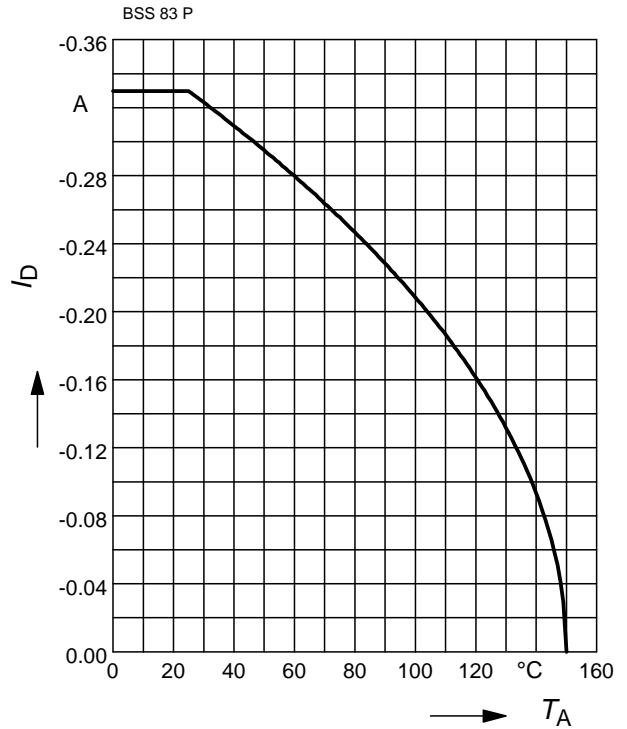
$$P_{tot} = f(T_A)$$



**Drain current**

$$I_D = f(T_A)$$

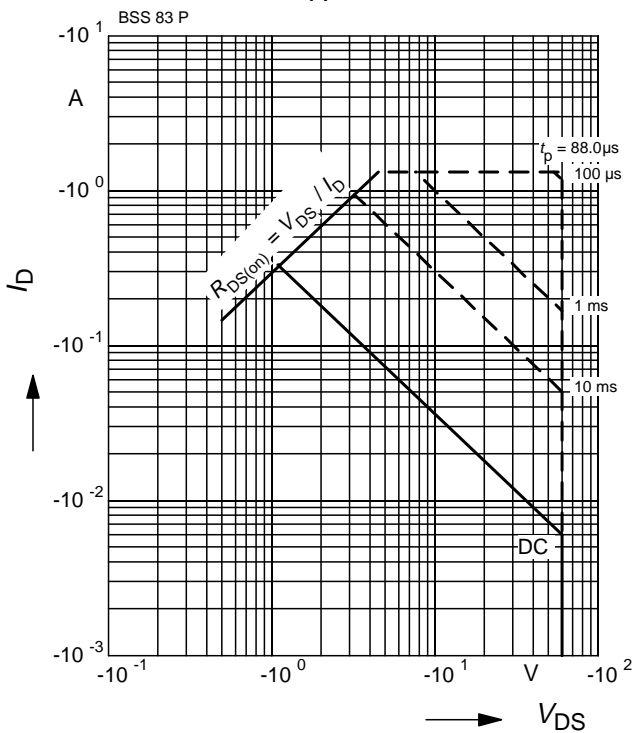
parameter:  $V_{GS} \geq 10 \text{ V}$



**Safe operating area**

$$I_D = f(V_{DS})$$

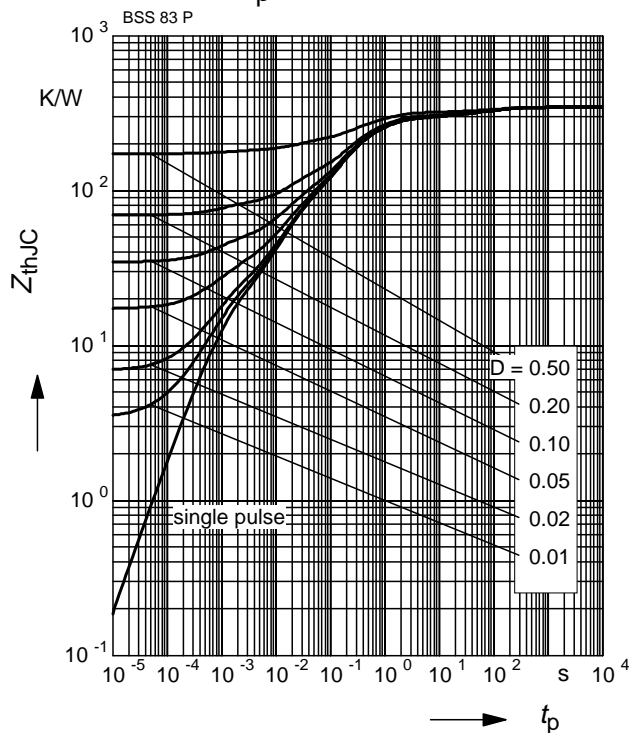
parameter:  $D = 0, T_A = 25 \text{ °C}$



**Transient thermal impedance**

$$Z_{thJC} = f(t_p)$$

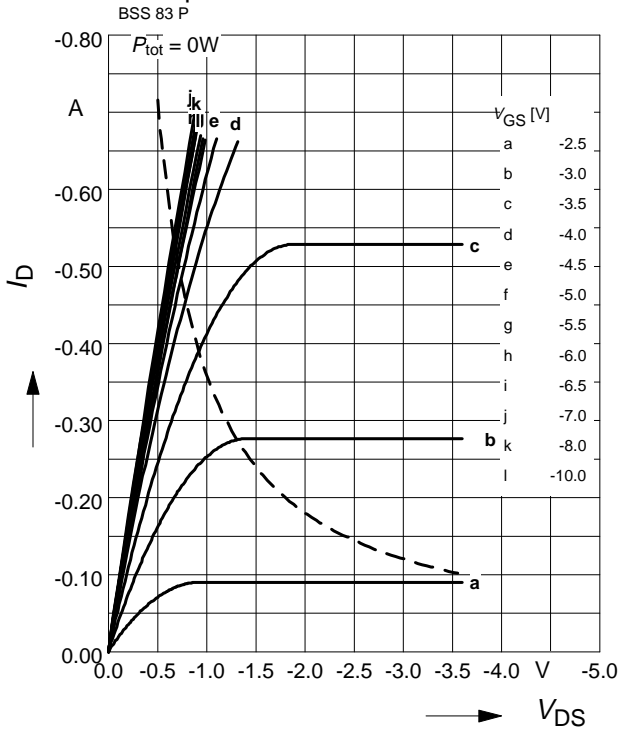
parameter:  $D = t_p/T$



**Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

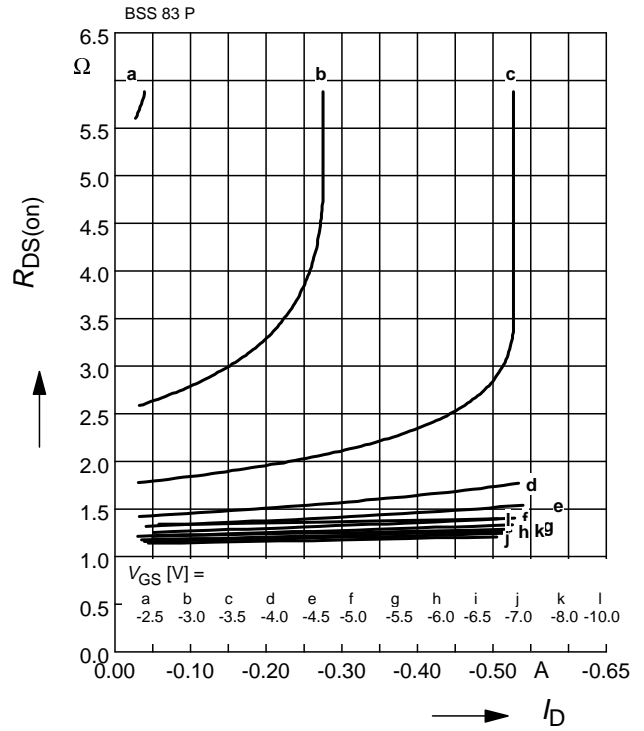
parameter:  $t_p = 80 \mu\text{s}$



**Typ. drain-source-on-resistance**

$R_{DS(on)} = f(I_D)$

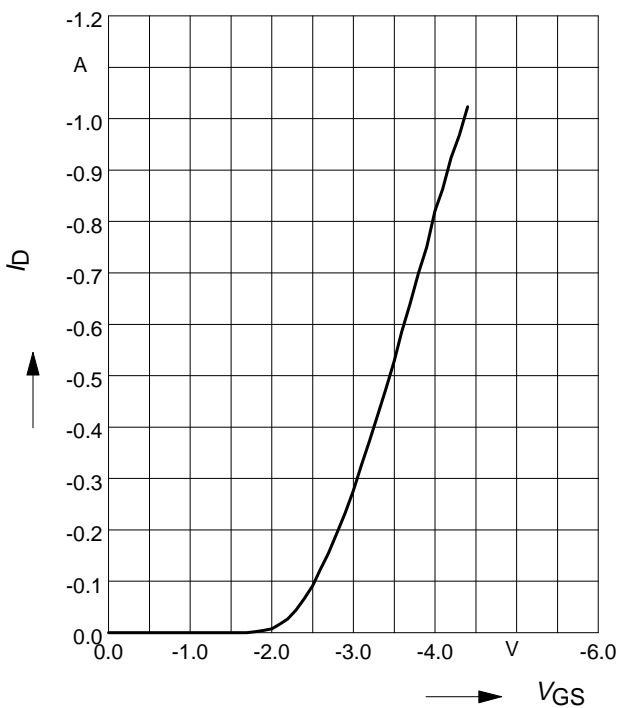
parameter:  $V_{GS}$



**Typ. transfer characteristics  $I_D = f(V_{GS})$**

$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

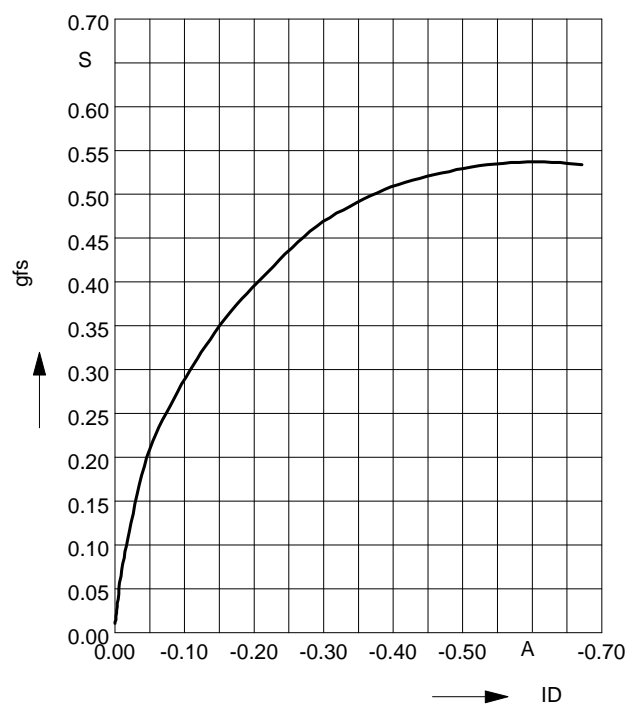
parameter:  $t_p = 80 \mu\text{s}$



**Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

parameter:  $g_{fs}$

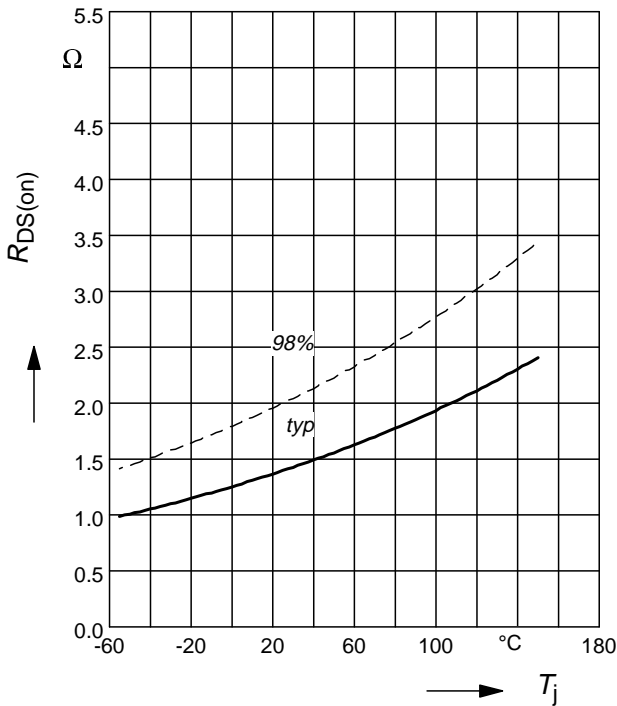


**Drain-source on-state resistance**

$$R_{DS(on)} = f(T_j)$$

parameter:  $I_D = -0.33 \text{ A}$ ,  $V_{GS} = -10 \text{ V}$

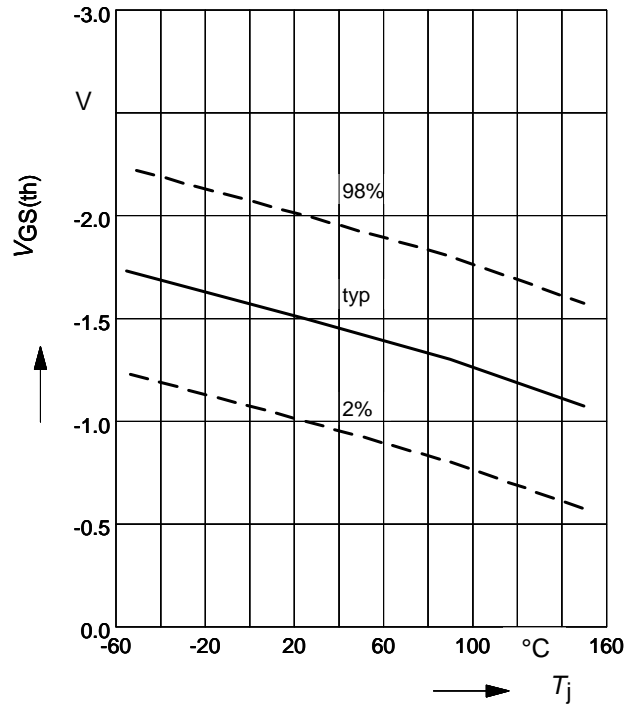
BSS 83 P



**Gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

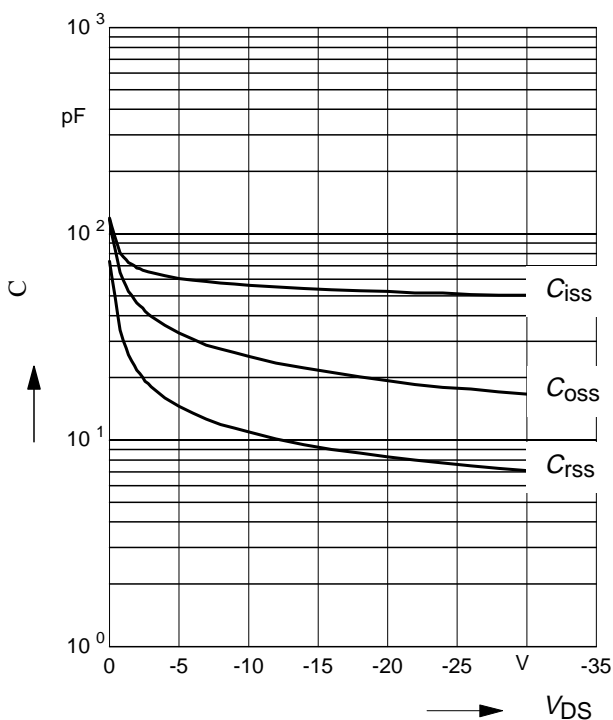
parameter:  $V_{GS} = V_{DS}$ ,  $I_D = -80 \mu\text{A}$



**Typ. capacitances**

$$C = f(V_{DS})$$

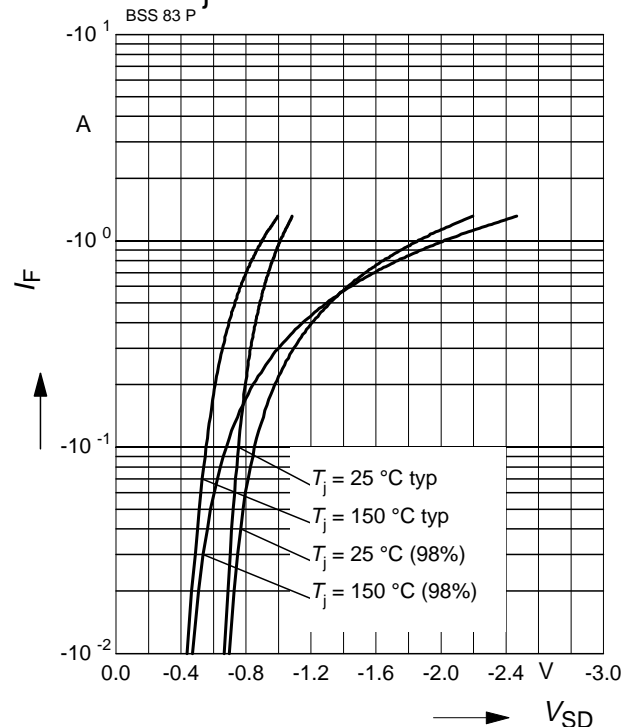
parameter:  $V_{GS} = 0 \text{ V}$ ,  $f = 1 \text{ MHz}$



**Forward characteristics of reverse diode**

$$I_F = f(V_{SD})$$

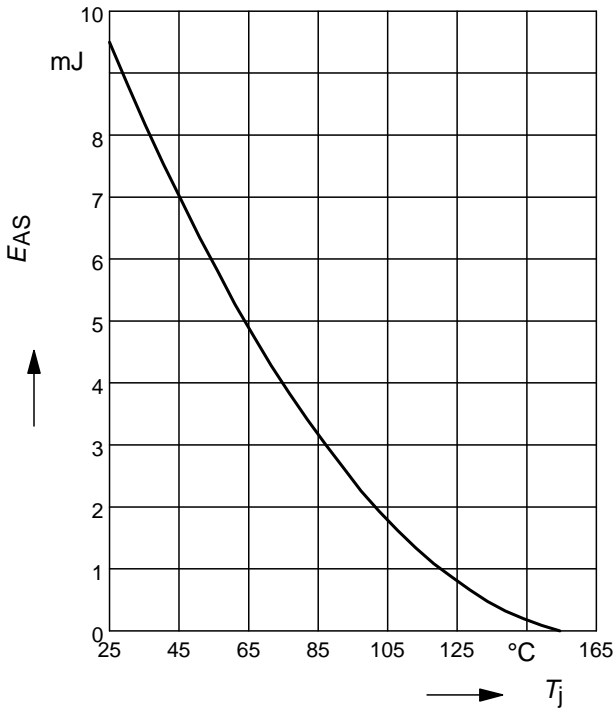
parameter:  $T_j$ ,  $t_p = 80 \mu\text{s}$



**Avalanche energy**

$$E_{AS} = f(T_j)$$

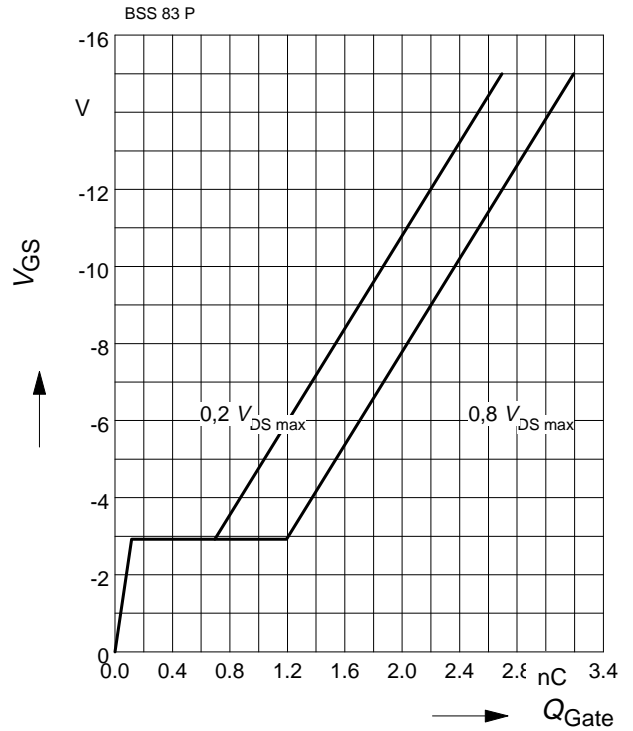
para.:  $I_D = -0.33 \text{ A}$  ,  $V_{DD} = -25 \text{ V}$  ,  $R_{GS} = 25$



**Typ. gate charge**

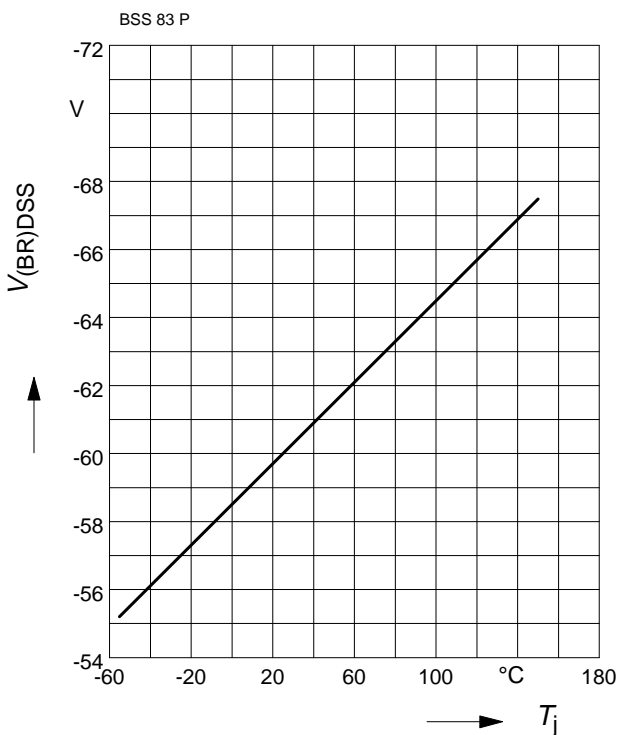
$$V_{GS} = f(Q_{Gate})$$

parameter:  $I_D = -0.33 \text{ A}$  pulsed



**Drain-source breakdown voltage**

$$V_{(BR)DSS} = f(T_j)$$





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